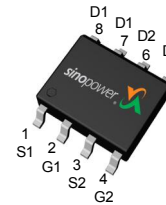


Dual N-Channel Enhancement Mode MOSFET

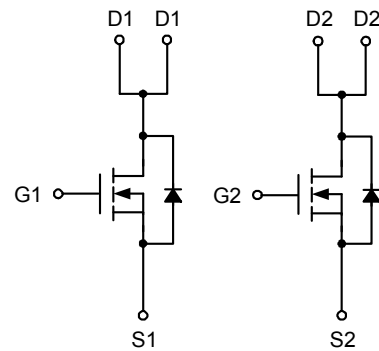
Features

- 30V/11.2A,
 $R_{DS(ON)} = 9m\Omega(max.) @ V_{GS} = 10V$
 $R_{DS(ON)} = 12m\Omega(max.) @ V_{GS} = 4.5V$
- Reliable and Rugged
- Lead Free and Green Devices Available
(RoHS Compliant)
- 100% UIS Tested

Pin Description



Top View of SOP-8



N-Channel MOSFET

Applications

- Power Management in Notebook Computer, Portable Equipment and Battery Powered Systems.

Ordering and Marking Information

SM4802DS □□-□□ □ Assembly Material Handling Code Temperature Range Package Code	Package Code K : SOP-8 Operating Junction Temperature Range C : -55 to 150 °C Handling Code TR : Tape & Reel Assembly Material G : Halogen and Lead Free Device
SM4802DS K : 4802 XXXXX	XXXXX - Lot Code

Note : SINOPOWER lead-free products contain molding compounds/die attach materials and 100% matte tin plate termination finish; which are fully compliant with RoHS. SINOPOWER lead-free products meet or exceed the lead-free requirements of IPC/JEDEC J-STD-020D for MSL classification at lead-free peak reflow temperature. SINOPOWER defines "Green" to mean lead-free (RoHS compliant) and halogen free (Br or Cl does not exceed 900ppm by weight in homogeneous material and total of Br and Cl does not exceed 1500ppm by weight).

SINOPOWER reserves the right to make changes to improve reliability or manufacturability without notice, and advise customers to obtain the latest version of relevant information to verify before placing orders.

Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$ Unless Otherwise Noted)

Symbol	Parameter		Rating	Unit
V_{DSS}	Drain-Source Voltage		30	V
V_{GSS}	Gate-Source Voltage		± 20	
I_D^a	Continuous Drain Current ($V_{GS}=10V$)	$T_A=25^\circ\text{C}$	11.2	A
		$T_A=70^\circ\text{C}$	9	
I_{DM}^a	300 μs Pulsed Drain Current ($V_{GS}=10V$)		40	
I_S^a	Diode Continuous Forward Current		1	
I_{AS}^b	Avalanche Current (Single Pulse)		13	
E_{AS}^b	Avalanche Energy, Single Pulse ($L=0.5mH$)		42.25	mJ
T_J	Maximum Junction Temperature		150	$^\circ\text{C}$
T_{STG}	Storage Temperature Range		-55 to 150	
P_D^a	Maximum Power Dissipation	$T_A=25^\circ\text{C}$	1.7	W
		$T_A=70^\circ\text{C}$	1.08	
$R_{\theta JA}^a$	Thermal Resistance-Junction to Ambient	$t \leq 10s$	48	$^\circ\text{C/W}$
		Steady State	74	
$R_{\theta JL}$	Thermal Resistance-Junction to Lead	Steady State	32	

Note a : Surface Mounted on 1in² pad area, $t \leq 10\text{sec}$.

Note b : UIS tested and pulse width limited by maximum junction temperature 150°C (initial temperature $T_J=25^\circ\text{C}$).

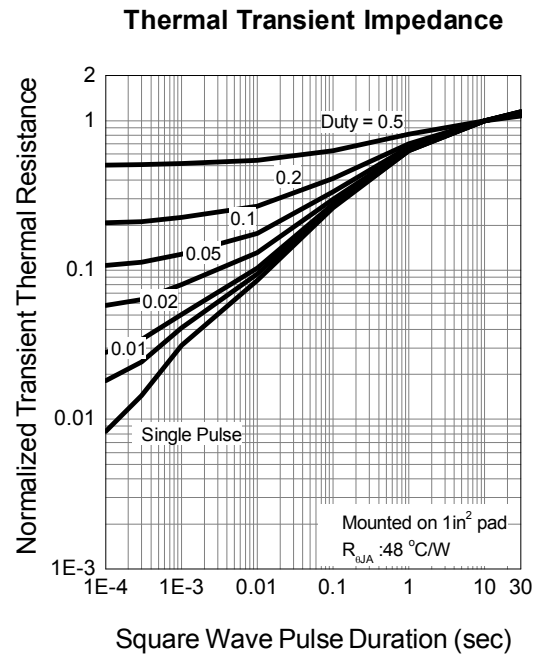
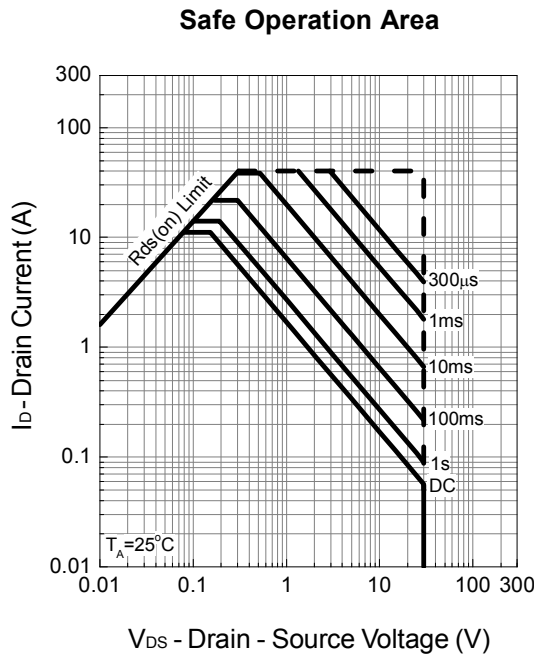
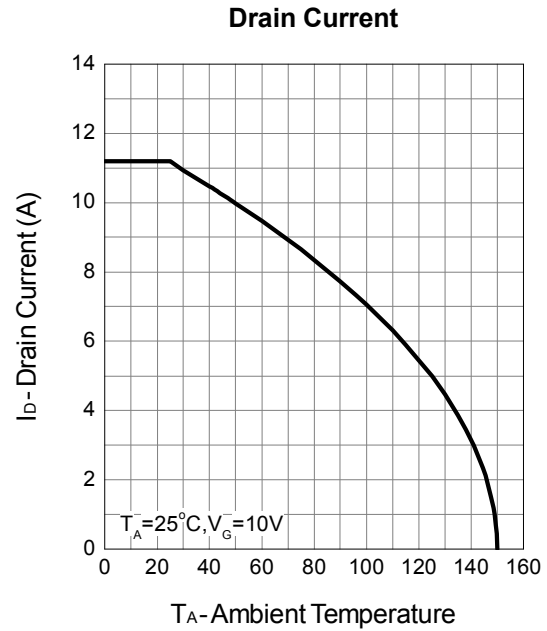
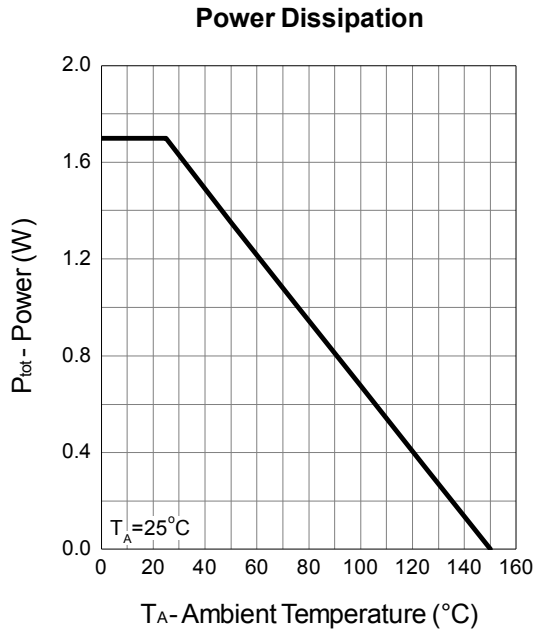
Electrical Characteristics (T_A = 25°C Unless Otherwise Noted)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =250μA	30	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =24V, V _{GS} =0V	-	-	1	μA
		T _J =85°C	-	-	30	
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =250μA	1.3	1.8	2.5	V
I _{GSS}	Gate Leakage Current	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
R _{DS(ON)} ^a	Drain-Source On-state Resistance	V _{GS} = 10V, I _{DS} =15A	-	7.5	9	mΩ
		V _{GS} =4.5V, I _{DS} =10A	-	9.3	12	
G _{fs}	Forward Transconductance	V _{DS} =3V, I _{DS} =10A	-	40	-	S
Diode Characteristics						
V _{SD} ^a	Diode Forward Voltage	I _{SD} =15A, V _{GS} =0V	-	0.75	1.1	V
t _{rr} ^b	Reverse Recovery Time	I _{SD} =15A, dI _{SD} /dt=100A/μs	-	14	-	ns
Q _{rr} ^b	Reverse Recovery Charge		-	4.5	-	nC
Dynamic Characteristics ^b						
R _G	Gate Resistance	V _{GS} =0V,V _{DS} =0V,F=1MHz	-	1	-	Ω
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =15V, Frequency=1.0MHz	1000	1180	1400	pF
C _{oss}	Output Capacitance		160	190	220	
C _{rss}	Reverse Transfer Capacitance		90	115	140	
t _{d(ON)}	Turn-on Delay Time	V _{DD} =15V, R _L =15Ω, I _{DS} =1A, V _{GEN} =10V, R _G =6Ω	-	8	14	ns
t _r	Turn-on Rise Time		-	10	17	
t _{d(OFF)}	Turn-off Delay Time		-	27	42	
t _f	Turn-off Fall Time		-	8	12	
Gate Charge Characteristics ^b						
Q _g	Total Gate Charge	V _{DS} =15V, V _{GS} =10V, I _{DS} =15A	-	20	26	nC
	Total Gate Charge	V _{DS} =15V, V _{GS} =4.5V, I _{DS} =15A	-	9.5	-	
Q _{gth}	Threshold Gate Charge		-	1.9	-	
Q _{gs}	Gate-Source Charge		-	4	-	
Q _{gd}	Gate-Drain Charge		-	3.5	-	

Note a : Pulse test ; pulse width ≤ 300 μs, duty cycle ≤ 2%.

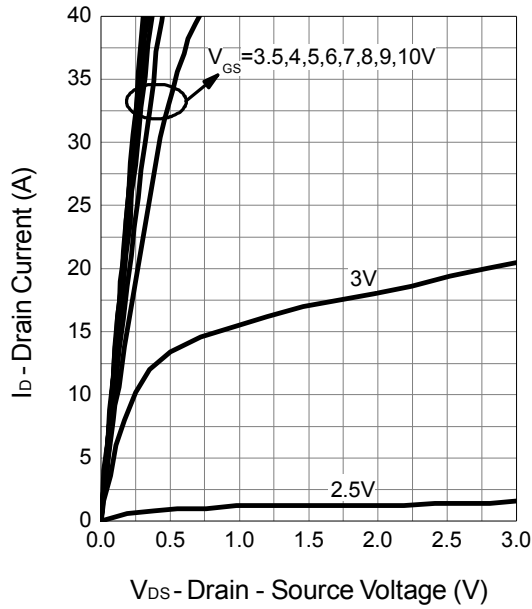
Note b : Guaranteed by design, not subject to production testing.

Typical Operating Characteristics

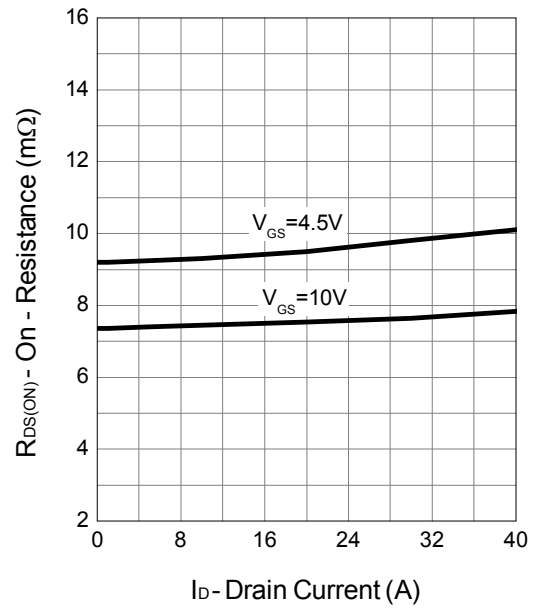


Typical Operating Characteristics (Cont.)

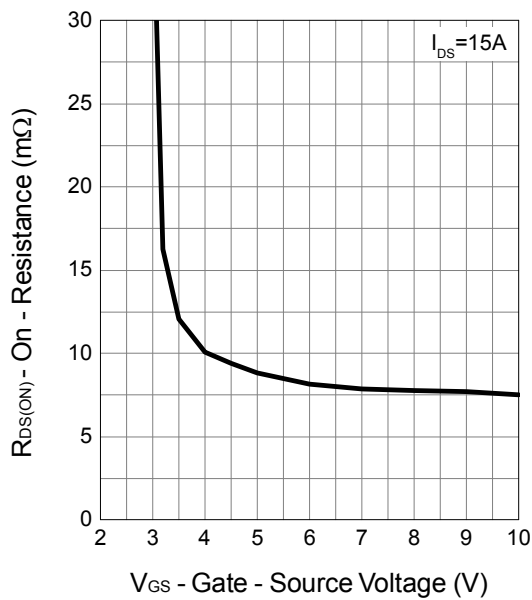
Output Characteristics



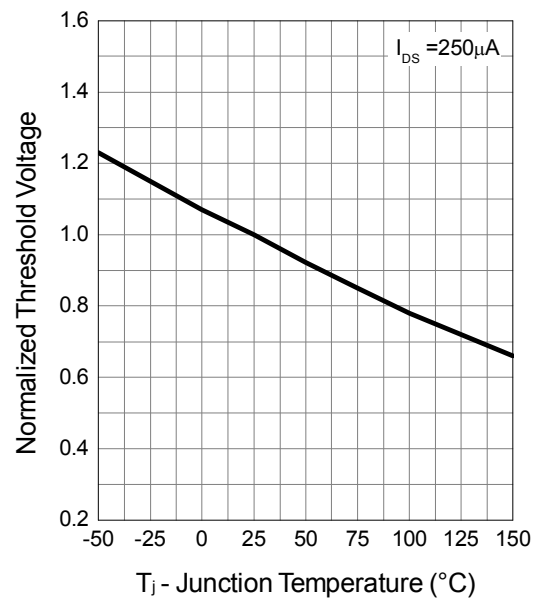
Drain-Source On Resistance



Gate-Source On Resistance

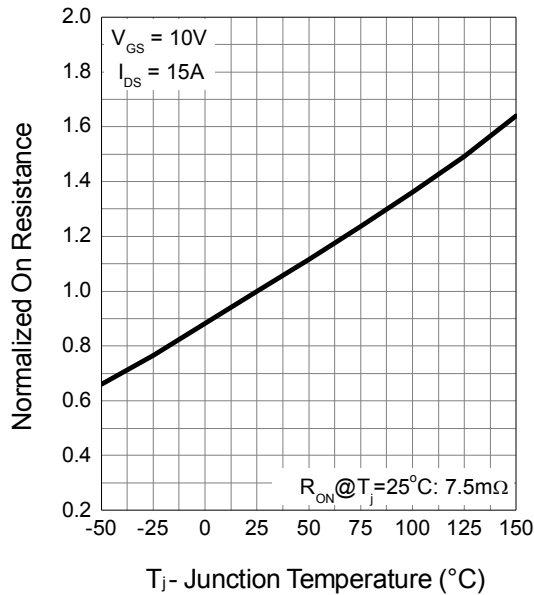


Gate Threshold Voltage

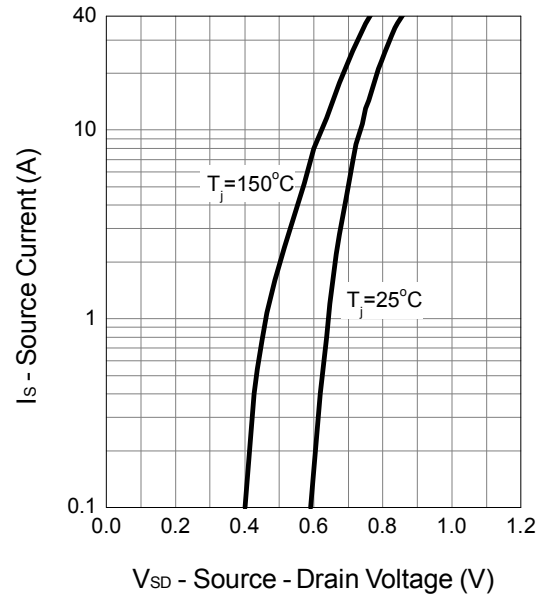


Typical Operating Characteristics (Cont.)

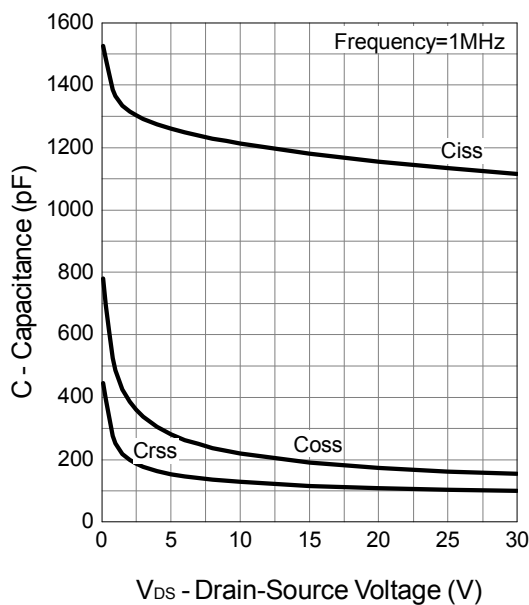
Drain-Source On Resistance



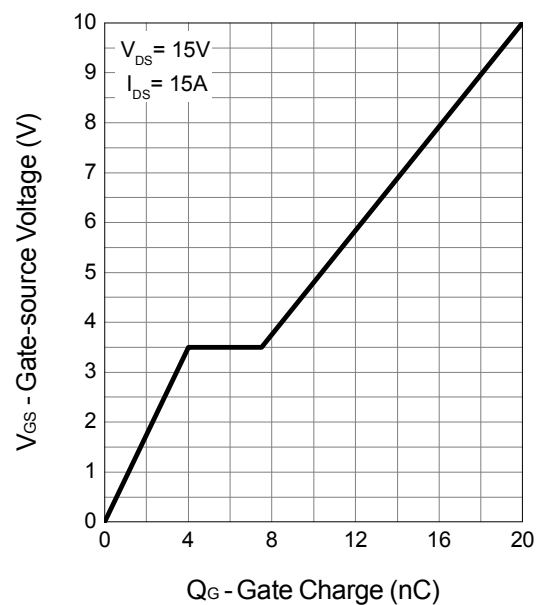
Source-Drain Diode Forward



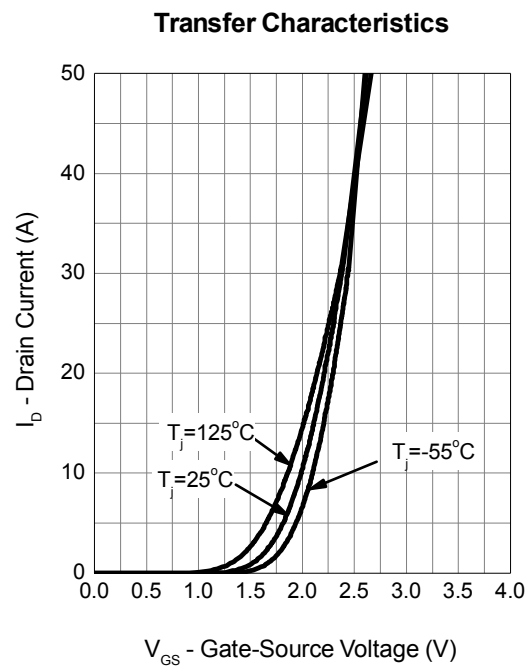
Capacitance



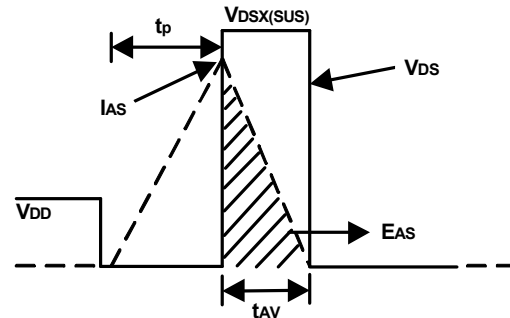
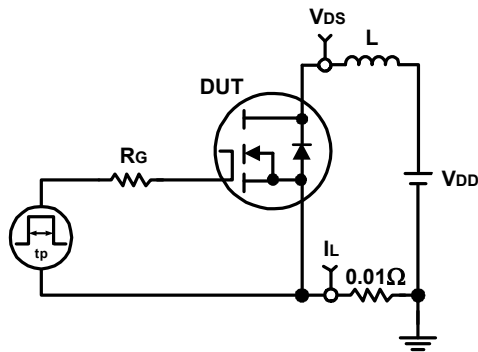
Gate Charge



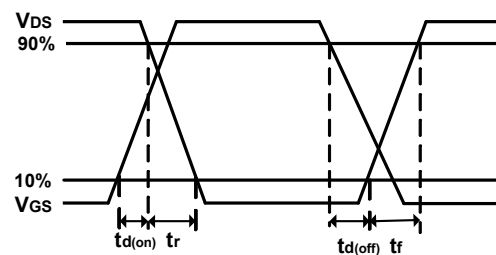
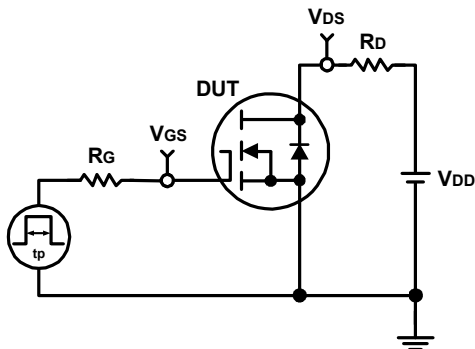
Typical Operating Characteristics (Cont.)



Avalanche Test Circuit and Waveforms



Switching Time Test Circuit and Waveforms



Disclaimer

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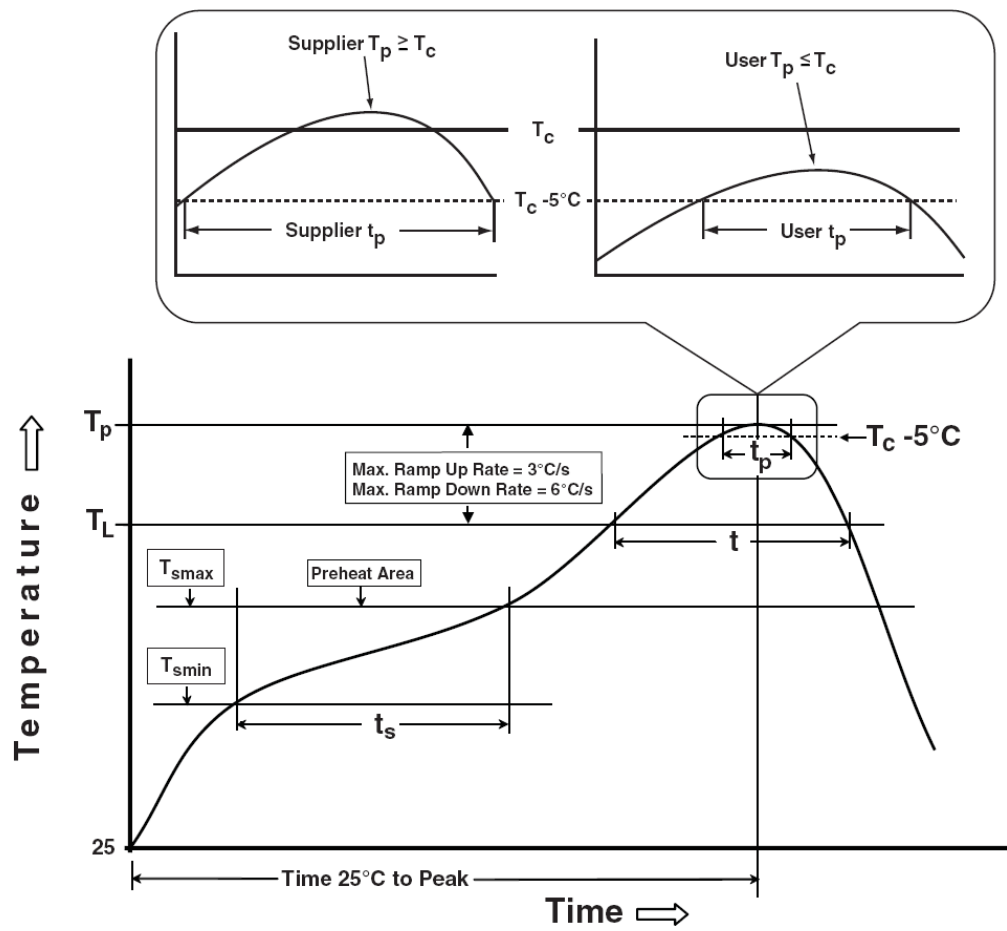
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Classification Profile



Classification Reflow Profiles

Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Preheat & Soak Temperature min (T_{smin}) Temperature max (T_{smax}) Time (T_{smin} to T_{smax}) (t_s)	100 °C 150 °C 60-120 seconds	150 °C 200 °C 60-120 seconds
Average ramp-up rate (T_{smax} to T_p)	3 °C/second max.	3°C/second max.
Liquidous temperature (T_L) Time at liquidous (t_L)	183 °C 60-150 seconds	217 °C 60-150 seconds
Peak package body Temperature (T_p)*	See Classification Temp in table 1	See Classification Temp in table 2
Time (t_p)** within 5°C of the specified classification temperature (T_c)	20** seconds	30** seconds
Average ramp-down rate (T_p to T_{smax})	6 °C/second max.	6 °C/second max.
Time 25°C to peak temperature	6 minutes max.	8 minutes max.
* Tolerance for peak profile Temperature (T_p) is defined as a supplier minimum and a user maximum. ** Tolerance for time at peak profile temperature (t_p) is defined as a supplier minimum and a user maximum.		

Table 1. SnPb Eutectic Process – Classification Temperatures (T_c)

Package Thickness	Volume mm ³ <350	Volume mm ³ ≥350
<2.5 mm	235 °C	220 °C
≥2.5 mm	220 °C	220 °C

Table 2. Pb-free Process – Classification Temperatures (T_c)

Package Thickness	Volume mm ³ <350	Volume mm ³ 350-2000	Volume mm ³ >2000
<1.6 mm	260 °C	260 °C	260 °C
1.6 mm – 2.5 mm	260 °C	250 °C	245 °C
≥2.5 mm	250 °C	245 °C	245 °C

Customer Service

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